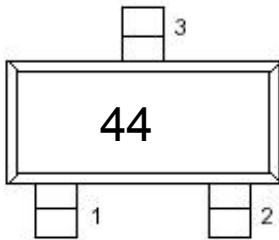


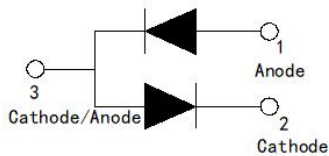
CDBAS40-04-ME

Schottky Diode

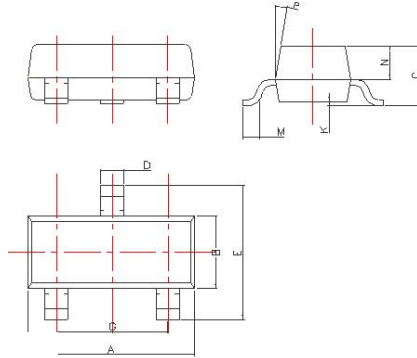
Marking: 44



Top view

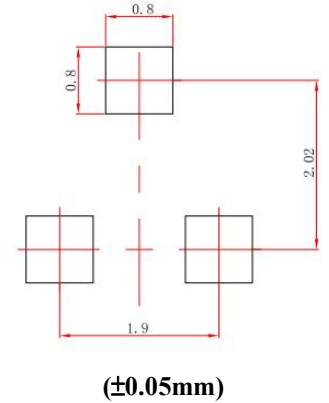


SOT-23 Dimension



DIM	Millimeters
A	2.85~3.04
B	1.30±0.10
C	1.00±0.10
D	0.45±0.05
E	2.25~2.55
G	1.90±0.1
K	0.00-0.10
M	0.20 min
N	0.60±0.10
P	7±2°

SOT-23 Suggested Layout



MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Reverse Voltage	V_R	40	Vdc
Peak Forward Current	I_F	350	mAdc
Peak Forward Surge Current	$I_{FM}(\text{surge})$	1.5	Adc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board(1) $T_A=25^\circ\text{C}$	P_D	225	mW
Total Device Dissipation Alumina Substrate,(2) $T_A=25^\circ\text{C}$	P_D	300	mW
Junction and Storage Temperature	$T_J,$ T_{stg}	150 , -55 ~50	$^\circ\text{C}$

- FR-5=1.0×0.75×0.062in, printed-circuit board.
- Alumina=0.4×0.3×0.024in, 99.5%alumina

CDBAS40-04-ME

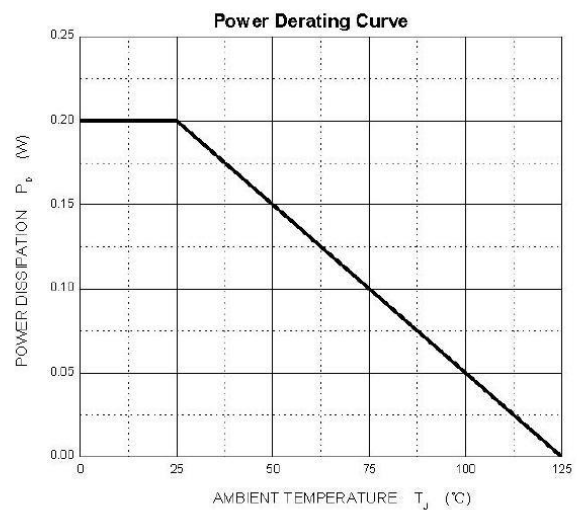
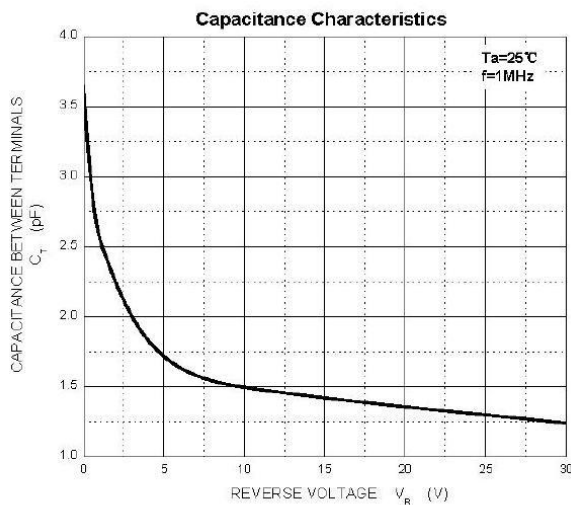
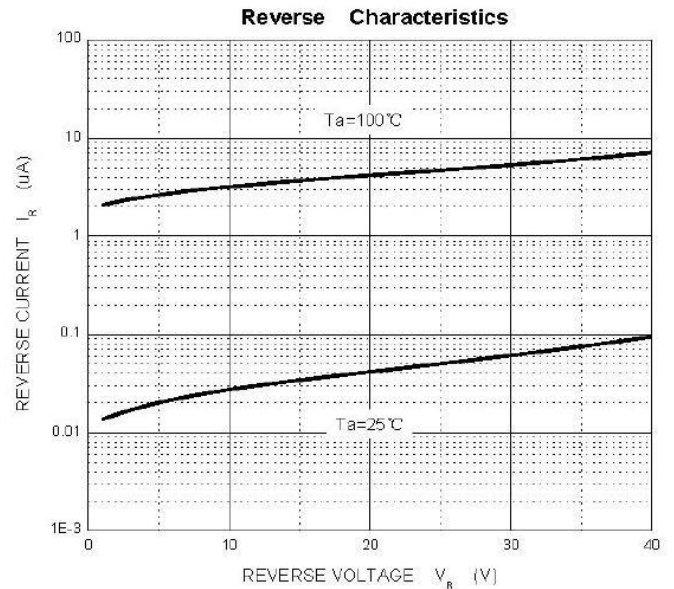
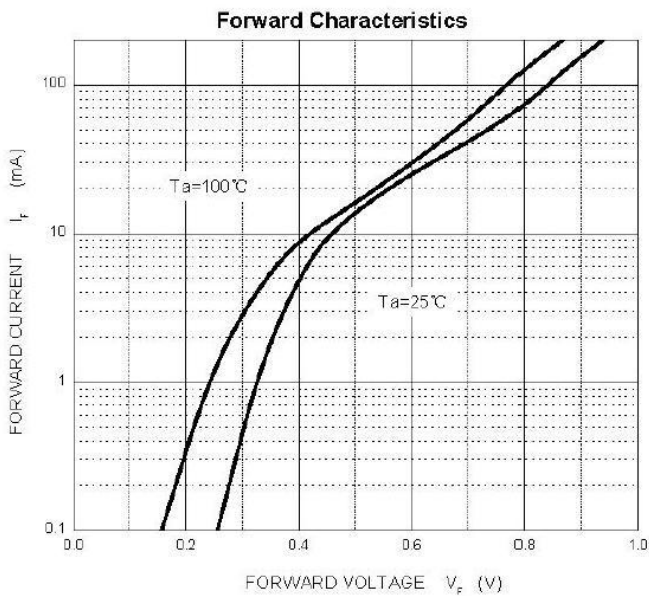
Schottky Diode

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Type	Max	Unit
Reverse Voltage Leakage Current	I _R	V _R =25Vdc	--	--	1.0	μA
Reverse Breakdown Voltage	V _(BR)	I _{BR} =10 μA dc	40	--	--	Vdc
Forward Voltage	V _F	I _F =20mA dc	--	--	370	mV
		I _F =200mA dc	--	--	600	
Total Capacitance	C _T	V _R =1V, f=1.0MHz	--	--	5.0	pF

Schottky Diode

Typical Performance Characteristics



Note: Specifications are subject to change without notice. For more detail and update, please visit our website.